

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hark C. Chan.)	Examiner: Unknown
)	
Serial No.: divisional of 10/262,728)	Group Art Unit: Unknown
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Filed: Herewith)	
)	
For: Shunt Connection to Emitter)	
)	

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Listed on the attached Form PTO-1449 is information known to applicant. Each reference cited herein was previously cited in parent applications and a copy of each reference was provided to the Examiner, or cited by the Examiner in an Office Action. No additional copies of the references are being submitted with this paper, but will be furnished upon the Examiner's request.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP 609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in section 1.56.

Date: Oct. 9, 200

Respectfully submitted,



Hark C. Chan
(Reg. N.: 35,477)

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Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	
Filing Date	
First Named Inventor	Andrew Horch
Art Unit	
Examiner Name	
Attorney Docket Number	C018-D-1

Sheet 1 of 2

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US- 3,943,549	3-9-1976	Jaecklin et al.	
		US- 4,165,517	8-21-1979	Temple et al.	
		US- 4,281,336	7-28-1981	Sommer et al.	
		US- 4,323,793	4-6-1982	Schutten et al.	
		US- 4,646,121	2-24-1987	Ogura	
		US- 4,829,357	5-9-1989	Kasahara	
		US- 4,864,168	9-5-1989	Kasahara et al.	
		US- 4,982,258	1-1-1991	Baliga	
		US- 5,412,228	5-2-1995	Baliga	
		US- 5,463,344	10-31-1995	Temple	
		US- 5,606,186	02-1997	Noda, Minoru	
		US- 4,825,272	04-1989	Lehmann, Erhard	
		US- 6,104,045	8-15-2000	Forbes et al.	
		US- 6,225,165	5-1-2001	Noble, et al.	
		US- 6,229,161	5-8-2001	Nemati et al.	
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				

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	Filing Date				
	First Named Inventor		Andrew Horch		
	Art Unit				
	Examiner Name				
Sheet	2	of	2	Attorney Docket Number	C018-D-1

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		K. DeMeyer, S. Kubicek and H. van Meer, Raised Source/Drains with Disposable Spacers for sub 100 nm CMOS Technologies, Extended Abstracts of International Workshop on Junction Technology 2001.	
		Mark Rodder and D. Yeakley, Raised Source/Drain MOSFET with Dual Sidewall Spacers, IEEE Electron Device Letters, Vol. 12, No. 3, March 1991	
		Yang-Kyu Choi, Daewon Ha, Tsu-Jae King and Chenming Hu, Nanoscale Ultrathin PMOSFETs with Raised Selective Germanium Source/Drain, IEEE Electron Device Letters, Vol. 22, No. 9, September 2001.	
		N. Lindert, Y. K. Choi, L. Chang, E. Anderson, W. C. Lee, T. J. King, J. Bokor, and C. Hu, Quasi-Planar FinFETs with Selectively Grown Germanium Raised Source/Drain, 2001 IEEE International SOI Conference, 10/2001	
		T. Ohguro, H. Naruse, H. Sugaya, S. Nakamura, E. Morifuji, H. Kimijima, T. Yoshitomi, T. Morimoto, H.S. Momose, Y. Katsumata, and H. Iwai, High Performance RF Characteristics of Raised Gate/Source/Drain CMOS with Co Salicide, 1998 Symposium on VLSI Technology Digest of Technical Papers	
		Hsiang-Jen Huang, Kun-Ming Chen, Tiao-Yuan Huang, Tien-Sheng Chao, Guo-Wei Huang, Chao-Hsin Chien, and Chun-Yen Chang, Improved Low Temperature Characteristics of P-Channel MOSFETs with Si1-xGex Raised Source and Drain, IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001	
		Nemati, Farid and Plummer, James, D., A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 6/1998	
		Nemati, Farid and Plummer, James, D., A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories, International Electron Device Meeting Technical Digest, 1999	
		Gribnikov, Z.S., Korobov, V.A., and Mitin, V.V., The Tunnel Diode as a Thyristor Emitter, Solid-State Electronics, Vol. 42, No. 9, 1998, pp. 1761-1763	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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